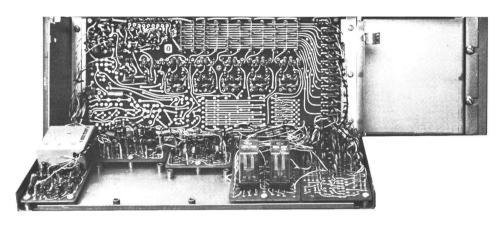
MASTR Progress Line

DECODER PANEL MODEL 4KC17A10



SPECIFICATIONS*

Transmitter Keying

Function Selection

Number of Functions

Frequency Response

Temperature Range

Dimensions (H x W x D)

3000 cps tone

Frequency-shift keying (1500, 2000 and 2500 cps)

12 maximum

 ± 3 db from 300 to 2750 cps, reference 1000 cps

 -30° C to $+60^{\circ}$ C (-22° F to $+140^{\circ}$ F)

5-1/4" x 19" x 4-3/4"

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

Decoder Panel Model 4KC17A10 provides up to 12 switching functions in MASTR Progress Line Remote and Repeater Base Station systems utilizing the Transistorized Control Console (XC Series) Model 4EC72A10.

The Decoder Panel contains the solid-state logic circuitry to decode the binary codes from the remote console for high-speed function switching, and to detect the 3-KC tone for keying the transmitter. The panel uses silicon transistors and diodes for added reliability. The Decoder Panel requires no adjustment.

An optional relay board is available for controlling a second receiver or other external functions as desired.

INTRODUCTION TO LOGIC CIRCUITS

A complete description of the logic circuits used in the Decoder Panel is available for the serviceman who may be unfamiliar with the operation of these circuits. This information is contained in LBI-3800, which is the Maintenance Manual for the Transistorized Control Console (XC Series). The manual includes a discussion of the following subjects:

- Solid-state switches
- Multivibrator circuits
- Binary counting and logic
- Logic circuits

It is suggested that anyone unfamiliar with these subjects study the information carefully, as a good understanding of the basic circuitry is essential in servicing the Decoder Panel.

CIRCUIT ANALYSIS

The Decoder Panel consists of the transistorized decoder circuitry, band-pass and low-pass filters FLl and FL2, and terminal boards for power and station interconnections. The decoder circuitry is located in a hinged assembly on the front of the panel. The filters and terminal boards are located on the back of the panel.

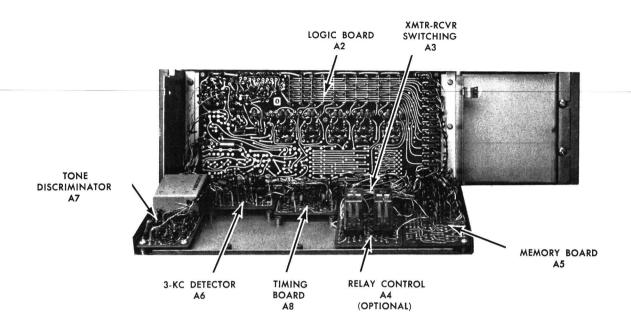


Figure 1 - Module Layout of Decoder Panel

In remote stations, the panel is normally mounted directly below the remote control panel. In repeater base stations, the panel is normally mounted below the repeater panel.

References to symbol numbers mentioned in this section can be found on the applicable Schematic Diagram, Outline Diagram and Parts List as listed in the Table of Contents.

POWER CIRCUITS

All operating voltages for the Decoder Panel are supplied by transmitter-receiver power supply Model 4EP38AlO, and are applied to the panel through TB708.

+13.4 VDC

The 13.4 volts DC is connected from TB708-3 to TB2-4 where it is filtered by C702 and R702 before being applied to the decoder circuits.

-5.4 VDC

A -45 volts DC is connected from TB708-4 to TB1-1 where the voltage is dropped by resistor R701 and regulated by zener diode VR701 to provide a -5.4 volts DC bias voltage. Filtering is provided by C702.

+18 VDC

When the optional relay control board is used, +18 volts is taken from TB708-1 as a supply voltage for relays K1 and K2.

CONTROL METHODS

Through the use of binary codes and tones, the Decoder Panel can provide up to 12 switching functions in addition to transmitter keying (see Figure 2).

Binary codes are used for multi-frequency, Channel Guard and other switching functions. A coded 3000-cps tone keys the transmitter.

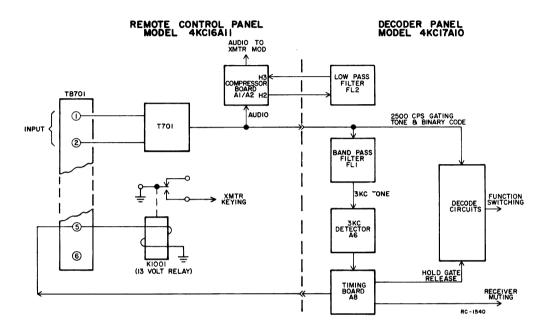


Figure 2 - Simplified Remote Switching & Keying Diagram

FUNCTION SELECTION

Pressing one of the function selection pushbuttons at the Transistorized Control Console applies a 3000-cps tone to the Decoder Panel for a minimum of 50 milliseconds (125 milliseconds for Repeater Base Stations). The tone is detected by 3-KC Detector Board A3, and applied to Timing Board A8. A switching circuit on the Timing Board grounds the receiver audio amplifier stage, muting the station receiver. A second switching circuit releases a hold gate so that the decode circuitry can accept a 2500-cps gating tone.

Releasing the pushbutton applies the 2500-cps gating tone to the panel for approximately 100 milliseconds. The gating tone releases a second hold gate so that the decoder circuitry can accept a binary code. A 40-millisecond, 2000-cps carrier tone follows the gating tone, and the carrier tone is followed by the binary tone code. The code is applied to the decoder circuitry to perform the desired switching function. A tone and code sequence waveform for the code 1-0-0-0-1 is shown in Figure 3.

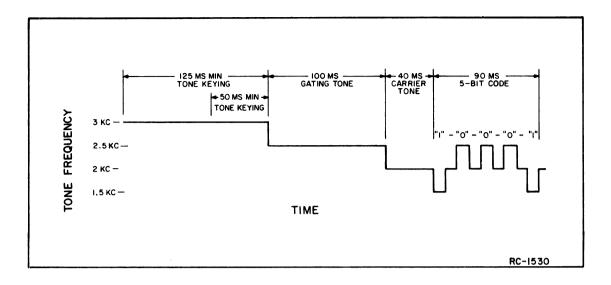


Figure 3 - Tone Sequence Waveform

TRANSMITTER KEYING

Keying the microphone at the remote console applies a 3000-cps coded tone to the Decoder Panel. The tone is coded at the remote console by switching it on for 60 milliseconds, switching it off for 60 milliseconds, and switching it on again for the duration of the transmission. A 100-millisecond switching interval is used in Repeater Base Stations. The 3000-cps keying tone is coded to prevent the transmitter from being keyed by the 3000-cps receiver muting tone that is applied to the Decoder Panel each time a function selection pushbutton is pressed at the remote console.

The coded 3000-cps tone is detected and converted to a DC voltage. The resultant DC voltage energizes a relay, keying the transmitter.

DECODE FUNCTION

The Decoder Panel contains the circuitry for changing a tone or code to a DC voltage for switching the transmitter or receiver frequency, disabling Channel Guard, or keying the transmitter. The following chart (Figure 4) contains a brief description of each circuit board in the Decoder Panel.

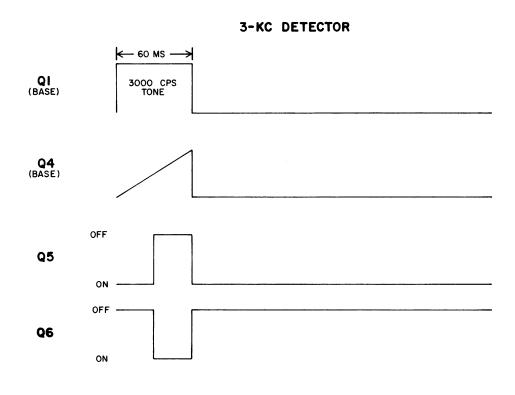
CIRCUIT BOARD	CIRCUIT DESCRIPTION
3 KC Detector A3	Contains the circuits to detect 3000-cps tones for driving the Timing Board.
Timing Board A8	Contains the circuits for muting the receiver, keying the transmitter, and releasing the hold gate on the Tone Discriminator board so that a code can be accepted.
Tone Discriminator A7	Contains the 1500 and 2500-cps tone detectors, the 2500-cps input hold gate, and 1500-cps and 2500-cps pulse generator circuits to drive the shift register.
Logic Board A2	Includes the decode matrix, 5-bit shift register, memory drivers, pulse delay and gating circuits.
Memory Board A5	Contains an encode gate, memory flip-flops and decode gate to drive the Transmitter-Receiver Switching board.
Transmitter- Receiver Switching Board A3	Contains the transistor Switching circuits for remote switching functions.
Relay Control Board A4 (Optional)	Contains two relays for controlling two receivers, and other external functions.

Figure 4 - Decode Function Chart

3-KC DETECTOR BOARD A6

Pressing one of the function selection pushbuttons at the Transistorized Control Console applies a 3000-cps tone to bandpass filter FLl and then to the 3-KC Detector board. The tone is amplified by Ql and Q2 and applied to the base of transistor Q3. Figure 5 contains simplified receiver muting waveforms.

The first positive half cycle of tone turns on Q3, and the positive emitter voltage back biases CR1. With CR1 back biased, C6 starts charging through R12. CR1 remains back biased for the duration of the tone, allowing C6 to charge up to a level sufficient to turn on Q4 in the "one-shot" (Schmitt Trigger). The time delay in turning on Q4 prevents noise falsing.



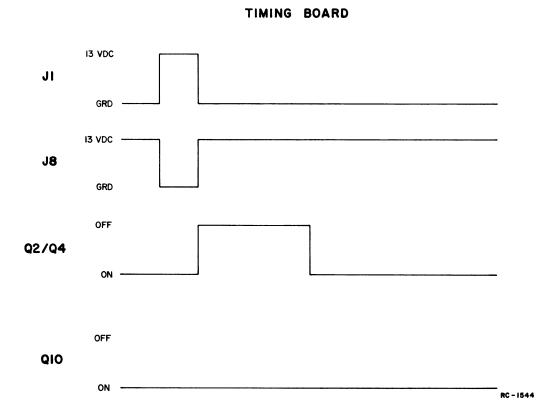


Figure 5 - Receiver Muting Waveforms

Turning on Q4 turns off Q5, and the collector voltage of Q5 rises to approximately 13 volts. The positive collector voltage is applied to the Timing Board through J9. The voltage also turns on Q6, causing its collector voltage to drop to near ground potential. This output is used for 3-KC keying only. The "one-shot" will remain switched for the duration of the 3000-cps tone (Q4 on and Q5 off).

TIMING BOARD A8

The positive pulse from the 3-KC Detector is applied to J1 on the Timing Board, charging C1. The instant the pulse ends, C1 begins to charge in the opposite direction. This forward biases CR1 which turns off Q2 and turns on Q3. Turning Q2 off applies a positive voltage to the base of Q1, turning it on. This grounds the base of the receiver audio PA stage and mutes the receiver. Q2 will remain off and Q3 on for approximately 250 milliseconds, keeping the receiver muted until the entire code has been received. Turning Q3 on turns off Q4 which removes a ground from the Tone Discriminator board so that the 2500-cps gating tone will be accepted.

TONE DISCRIMINATOR A7

The incoming tone and code is connected to tone input jack Jl on the Tone Discriminator where it is coupled through a limiter circuit (CR9, CR10 and R34) amplifiers Ql and Q2. DC feedback through R2, R6, and R35 provides a symmetrical squarewave output (proportional to the input) that is applied to the base of emitter-follower Q13.

Discriminator transformer Tl has a 2500-cps output and a 1500-cps output. The 2500-cps gating tone preceding the code is fed from pin 5 of Tl to the base of emitter-follower Q3 as a series of pulses. The first pulse turns on Q3, shorting capacitor Q3. The positive voltage at the emitter of Q3 back biases CRl and turns on Q5. In the interval between pulses, Q3 turns off but C3 charging through R10 keeps CRl back biased and Q5 on until the next pulse. Q5 and Q7 are connected as a "one-shot" multivibrator, and turning Q5 on turns Q7 off. The 2500-cps tone pulses have been converted to a single positive pulse at the collector of Q7. Figure 6 contains simplified waveforms of the code 1-0-0-0-1 applied to the Tone Discriminator Board.

The 100-millisecond gating pulse turns on Q9 and back biases CR5. This allows C7/Cl2 to start charging through R25. The capacitor charges up to approximately 5 volts in a minimum of 40 milliseconds to turn on Q10. Turning Q10 on discharges C8 and keeps it discharged until the gating pulse ends. Then Q10 cuts off and C8 starts charging through R26 so that a positive pulse appears at the junction of C8 and R28. The positive pulse forward biases CR8 and switches the "one-shot" (turns Q12 on and Q11 off). With W11 off, the positive collector voltage is applied from the decode gate jack (J7) to the Delay circuit input (J6) on the Logic Board, releasing the hold on the Delay circuit. The "one-shot" remains triggered (Q11 off and Q12 on) for approximately 200 milliseconds, keeping the Delay circuit open to accept an entire code that follows the gating tone. The 40-millisecond minimum charging time for C7/C12 prevents a noise pulse from triggering the one-shot.

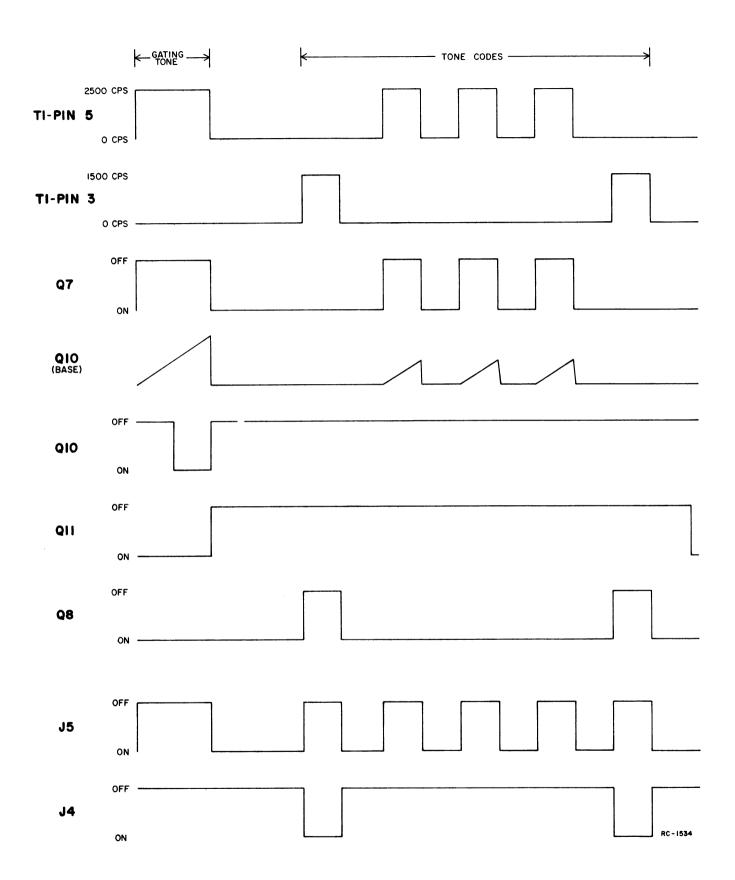


Figure 6 - Tone Discriminator Waveforms

With the 1-0-0-0-1 applied to the Tone Discriminator, a 10-millisecond, 1500-cps tone burst from T1-pin 3 is applied to Q4, Q6 and Q8, which is identical to the 2500 cps circuit Q3, Q5 and Q7. The positive pulse at the collector of Q8 is coupled through "OR" gate diode CR4 to the decode clock jack J5.

Following the 1500-cps tone, a 2500-cps tone burst from Tl-pin 5 is applied to Q3, Q5 and Q7, resulting in a 10-millisecond positive pulse at the collector of Q7. The pulse is coupled through "OR" gate diode CR3 to the decode clock output jack J5. The entire 5-bit code is converted by the two circuits and "added" by the "OR" gate diodes to supply five positive clock pulses to drive the shift register.

In addition to the clock pulses, a negative pulse from the collector of Q6 is applied to "1" output jack J4 whenever a 1500-cps tone is applied to the Tone Discriminator. This negative pulse is connected to J3 on the Logic Board.

LOGIC BOARD A2

Both the positive clock pulses and the negative "1" pulses are applied to the Logic Board simultaneously. The negative "1" pulse from input jack J3 turns off Q13 which turns on Q14 in the 0/1 Load circuit. This sets the circuit to load a "1" into the shift register whenever the first pulse is applied to the shift register pulse line. Refer to Figure 7 for the Logic Board decode waveforms for the code 1-0-0-0-1.

Pulse shaper Ql is normally off, keeping Cl discharged through CR2. The first clock pulse applied to the base of Ql turns the transistor on. This back biases CR2, so that Cl charges through R3 and turns on Q2 in the Delay one-shot, turning off Q3. The pulse delay due to Cl charging protects the stage against noise falsing. Switching Q3 off applies a positive pulse to Pulse Mixer Q12 where it is inverted and applied to the shift register pulse line to shift in the first code bit.

The decode clock pulses are also fed from J2 to the base of Q4 in the Interpulse Timer circuit. The first pulse turns on Q4, which acts as a short across C3. The positive voltage at the emitter of Q4 back biases CR5 which turns on Q5 and turns off Q6. In the interval between clock pulses, Q4 turns off and C3 charges through R11 to keep CR5 back biased and Q5 turned on. Keeping Q5 turned on applies a ground through CR8 to the base of Q9, keeping it turned off. This releases the zero hold on Reset Gate diodes CR26, CR45, CR58, CR69 and CR82. The ground also forward biases CR9 and Read Gate diodes CR14 through CR25, disabling the Decode Matrix until a complete code has been shifted into the register. As long as Q5 is kept on by the five clock pulses and the charging of C3, the code will be shifted into the register. However, if a code should be interrupted or a clock pulse missing, Q5 will turn off and Q9 will turn on as soon as the Read One-Shot releases. This restores the zero hold on the Decode Matrix and releases the ground on the Read Gate diodes, and another code will have to be received to restart the cycle.

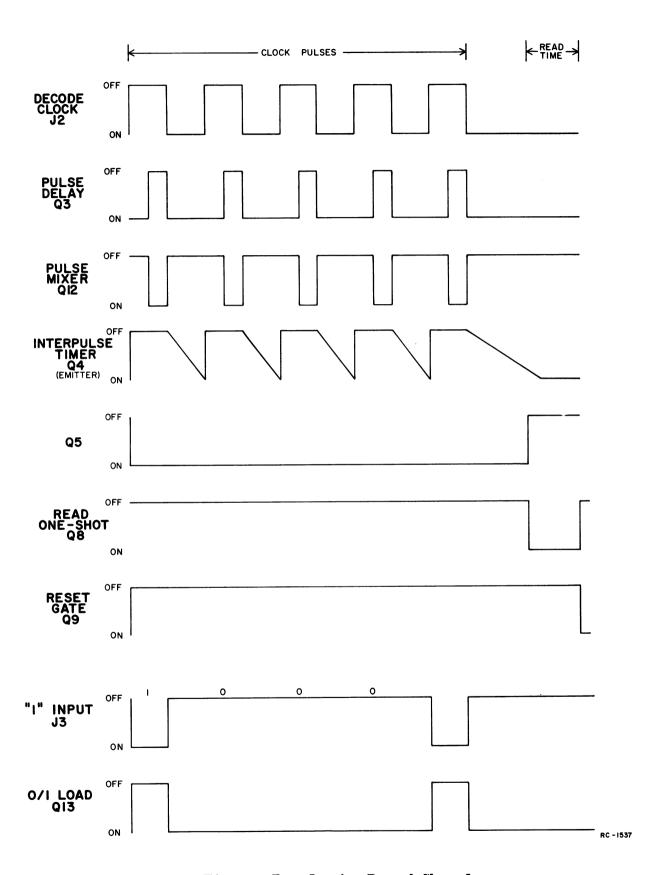


Figure 7 - Logic Board Waveforms

At the end of the clock pulses, Q4 and Q5 turn off. This lets Q6 turn on and discharges C4, which starts charging in the opposite direction through CR6. This turns off Q7 and turns on Q8 in the Read One-Shot, forward biasing CR7 and keeping Q9 turned off and keeping the zero hold off in the matrix. The one-shot remains switched for 30 milliseconds which is the read time for the matrix. The code that has been shifted into the register is applied to the Decode Matrix and appears as a positive pulse at the base of one of the Memory Drivers (Q35-Q46) where it is inverted and applied to the Memory Board as a negative-going pulse. After 30 milliseconds, the one-shot switches back to its original state (Q7 and Q8 off). Q9 turns on and switches the shift register back to the "0" state.

MEMORY BOARD A5

The Memory Board contains two, four or six flip-flops for four, eight or twelve remote switching functions. Each of the flip-flops has an input and output diode "AND" Gate Matrix. By adding or deleting these diodes, the flip-flops can be connected for four interlocked functions (only one of the four functions on at a time), for groups of two interlocked functions (only one transistor on in each pair), or for a combination of two and four interlocked functions.

Applying binary code 1 - 0 - 0 - 0 - 1 to the Decoder Panel results in a negative-going, 30-millisecond pulse at J25 on the Logic Board. The pulse is connected to J4 on the Memory Board where it forward biases diodes CR2 and CR6, turning on transistors Q2 and Q3 which turns off Q1 and Q4. The 13 volts at the collector of the OFF transistors reverse biases CR26 and CR30, allowing the potential at output jack J16 to rise to 13 volts. J16 will remain at this potential as long as Q1 and Q4 are turned off. Q1 and Q4 will remain off with Q2 and Q3 on until a different code is applied to the Decoder Panel. Output jacks J17, J18, and J19 are held at ground potential by the collectors of the ON transistors.

TRANSMITTER-RECEIVER SWITCHING BOARD A3

Receiver Switching

The positive voltage from the Memory Board is connected to J2 on the Transmitter-Receiver Switching Board. From J2, the voltage is connected through J1 to the receiver oscillator circuit to turn on the F1 oscillator.

In Channel Guard applications, "OR" Gate diodes CR1 thru CR4 and transistors Q1, Q2 and Q3 are provided for turning the Channel Guard on or off. For example, if the F1 frequency is selected, the positive voltage at J2 forward biases diode CR1 and turns on Q1. If the Channel Guard pushbutton at the Remote Console is pressed in, a positive voltage from the Memory Board is applied to the base of Q2, keeping the transistor on. This keeps Q3 turned on (its collector at ground potential), allowing the receiver Channel Guard circuit to operate.

Pressing the Channel Guard OFF pushbutton at the Remote Control Console switches off the positive voltage at the base of Q2, turning off Q2 and Q3. Removing the ground at the collector of Q3 disables the receiver Channel Guard. The receiver operates on noise squelch only, permitting the dispatcher to monitor the channel.

The Channel Guard function can be disabled for a particular receiver frequency by removing one of the "OR" Gate diodes.

Transmitter Switching

Pressing one of the transmitter frequency pushbuttons at the Remote Control Console causes a positive voltage to be applied to one of the transmitter switching input jacks (J13 through J16). Pressing the Tx-Fl pushbutton applies 13 volts to J13, turning on Q4. The collector of Q4 drops to near ground potential, and is connected through J9 to the transmitter oscillator circuit, to turn on the oscillator.

In Channel Guard applications, "OR" Gate diodes CR7 through CR10 and transistors Q8 and Q9 are provided for automatically turning on the Channel Guard whenever a frequency is selected. The positive voltage at J13 forward biases CR7, which turns on Q8 and Q9. The collector of Q9 goes to approximately +10 volts DC, turning on the Channel Guard.

The Channel Guard function can be disabled for a particular transmitter frequency by removing one of the "OR" Gate diodes.

RELAY CONTROL BOARD A4 (Optional)

The optional Relay Control Board is required for stations equipped with two separate receivers. A positive voltage from the Memory Board applied to the base of relay drivers Q1 or Q2 turns the transistor on, completing the ground path for the relay. Energizing the relay switches the selected receiver audio to output terminal TB710-2.

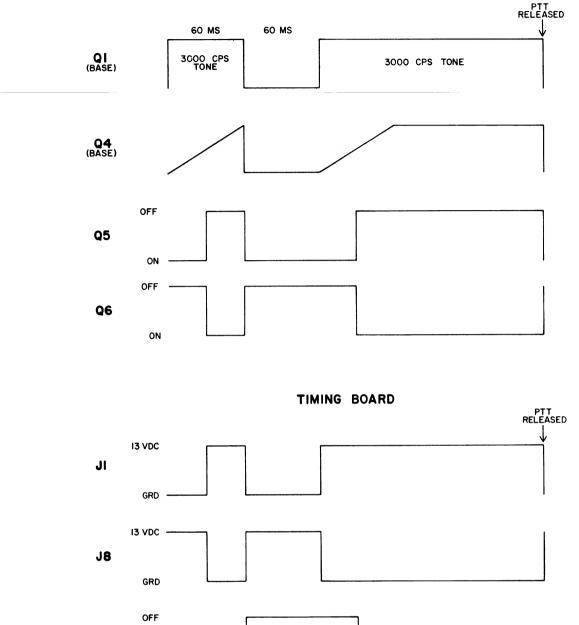
Each relay has four form "C" contacts connected to jacks on the Relay Control Board to permit connections for other external switching functions. The relays are rated at 1 amp with an inductive load at 29 volts DC, 2 amps with a resistive load, or 1 amp with a 115-volt AC load.

3-KC KEYING

3-KC DETECTOR

Keying the microphone at the Transistorized Control Console applies a coded 3000-cps tone to the Detector Board. This tone is detected in the same manner as the muting tone and results in a positive pulse at J9 and a ground at J6. Waveforms for the 3-KC keying are shown in Figure 8.

3-KC DETECTOR



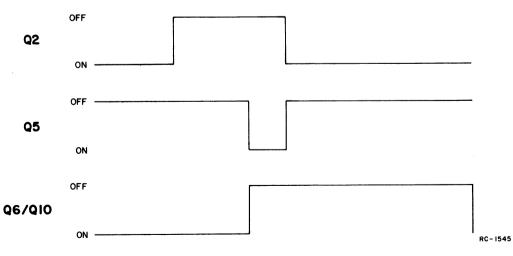


Figure 8 - 3 KC Keying Waveforms

TIMING BOARD

The positive pulse from the first portion of the 3000-cps tone switches Q2 off and Q3 on, which mutes the receiver and applies a positive voltage to the base of Q5. The second portion of the tone is detected and the ground at J8 turns on Q5. This causes C5 to charge, forward biasing CR3 which turns off Q6. The ground at J8 also disables Q7 which allows Q8 to turn on.

Turning Q6 off applies a positive voltage to the base of Q9, turning it on. This turns on Q10 and its collector voltage rises to 13 volts. In Remote Stations, this 13 volts is connected from J7 to the Remote Control Panel 4KCl6All where it energizes relay Kl001, keying the station transmitter.

In Radio Control Base Station Systems, the 13 volts is applied from the Decoder Panel on the Repeater Base Station to the Repeater Panel on the Repeater Control Station. The voltage is applied to a voltage divider and energizes the Carrier Operated Relay, keying the transmitter. A simplified tone keying diagram for repeater stations is shown in Figure 9.

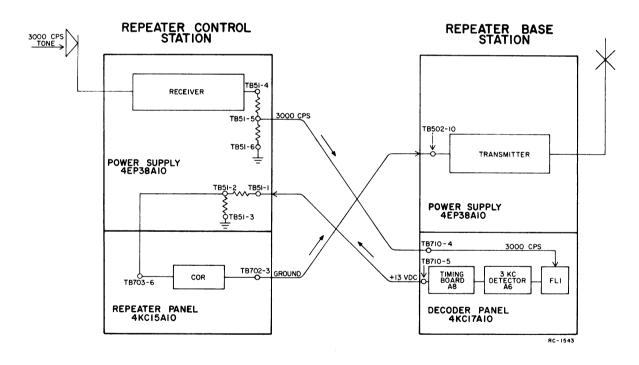


Figure 9 - Repeater Tone Keying Diagram

POWER SUPPLY MODIFICATIONS

In tone keying applications, filter-amplifier assembly FL1-Al and terminal board TB51 are added to power supply Model 4EP38A10. In stations with second receivers, a second filter-amplifier assembly is added to receiver power supply Model 4EP39A10.

Audio from the receiver is taken from the volume control (R511 on the EP-38-A or R502 on the EP-39-A), and is coupled through emitter-follower Q1 to low-pass filter FL1. The filter attenuates any 3000-cps signal from the station receiver to prevent noise from keying the transmitter or muting the receiver. The filter output is amplified by Q2 and applied to emitter-follower Q3. In remote stations, the output of Q3 is connected back to the station receiver. In repeater stations, the output connects to the audio coupler on the repeater panel.

MAINTENANCE

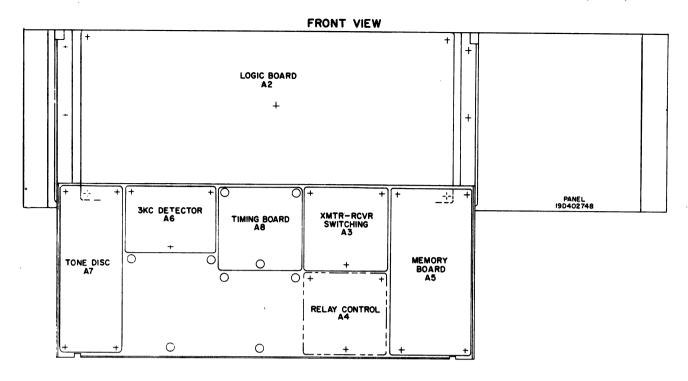
DISASSEMBLY

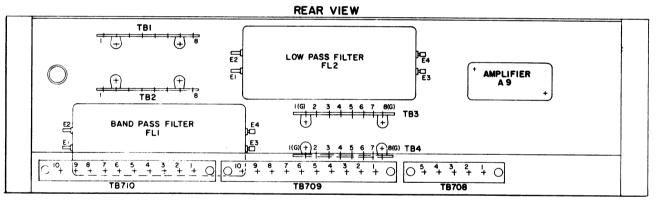
To gain access to the component boards in the Decoder Panel, spring open the retaining clips on each side of the assembly and lower the hinged front cover.

TROUBLESHOOTING

Specific troubleshooting procedures are available for the Decoder circuitry (see Table of Contents). The procedures include:

- DC voltage checks using a VTVM
- Waveform checks using an externally triggered oscilloscope.





MULTI-FREQUENCY CONNECTIONS

HARNESS 19A122455G1-G6

			To	O XMTR-RCVR SWI	TCHING BOARD	13	
FROM MEMORY BOARD A5	WIRE COLOR	3- OR 4-FREQ XMTR & RCVR (GI)	2-FREQ XMTR 2-FREQ RCVR (G2)	2-FREQ XMTR I-FREQ RCVR W OR W/O C.G. (G3)	I-FREQ XMTR 2-FREQ RCVR (G4)	2-FREQ XMTR I-FREQ RCVR NO C.G. (G5)	2-FREQ XMTR 2-RECEIVERS (G6) *
JI6	G	J2	J2	JI3	J2	J2	
JI7	G	J4	J4			J13	
JI8	G	J6	J6		J2I	JI4	
J19	G	J8		. JI4	J4	J4	
J20	G	JI3	JI3				J13
J2I	G	JI4					
J22	G	J15	J21				
J23	G	J16	J14				JI4
J24	G	J2I					

* ALSO REQUIRES G4 HARNESS

RC-1539

OUTLINE DIAGRAM

DECODER PANEL MODEL 4KC17A10

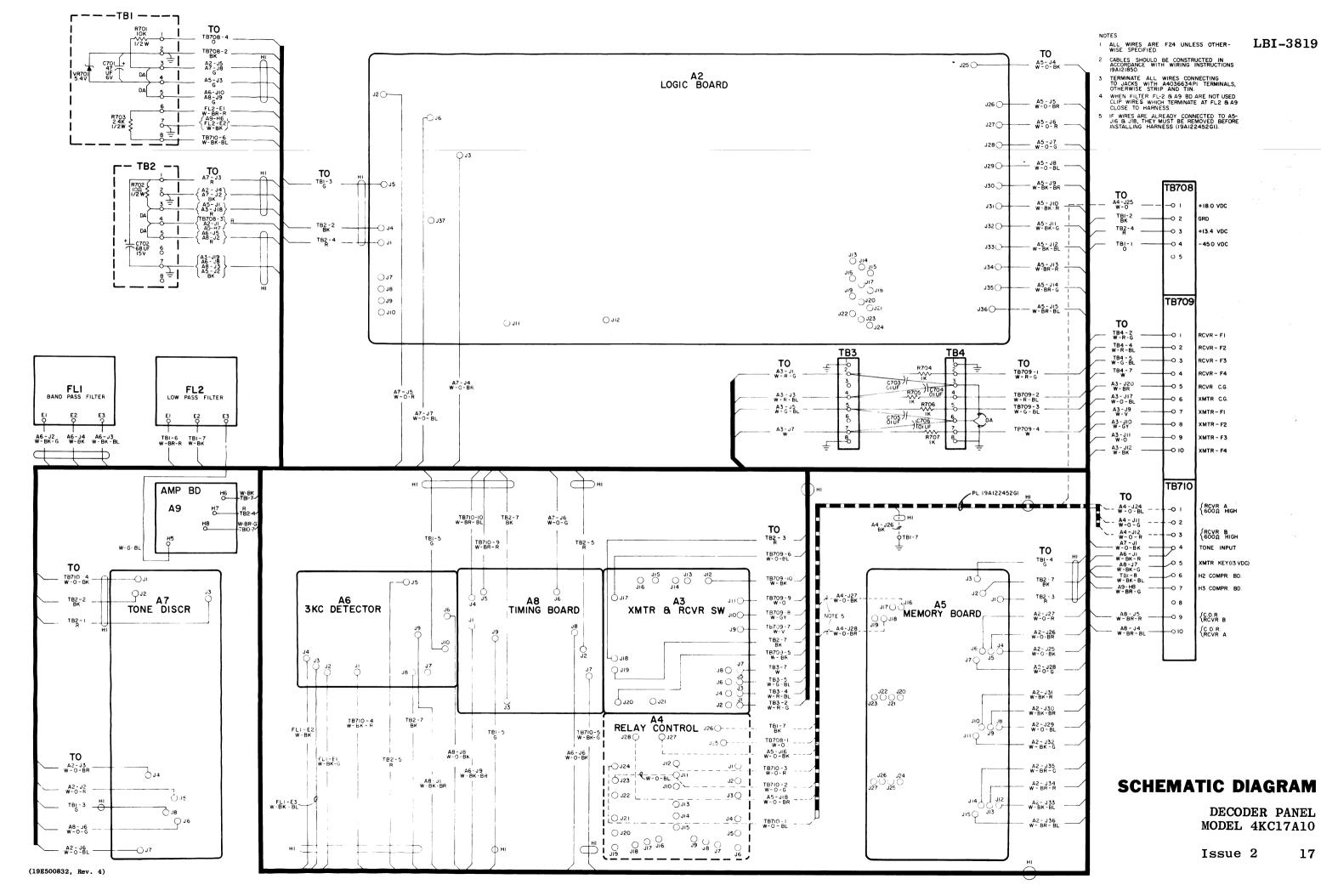
PARTS LIST

LBI-3818

CHASSIS MODEL 4KC17A10 PL-19D402748-G1

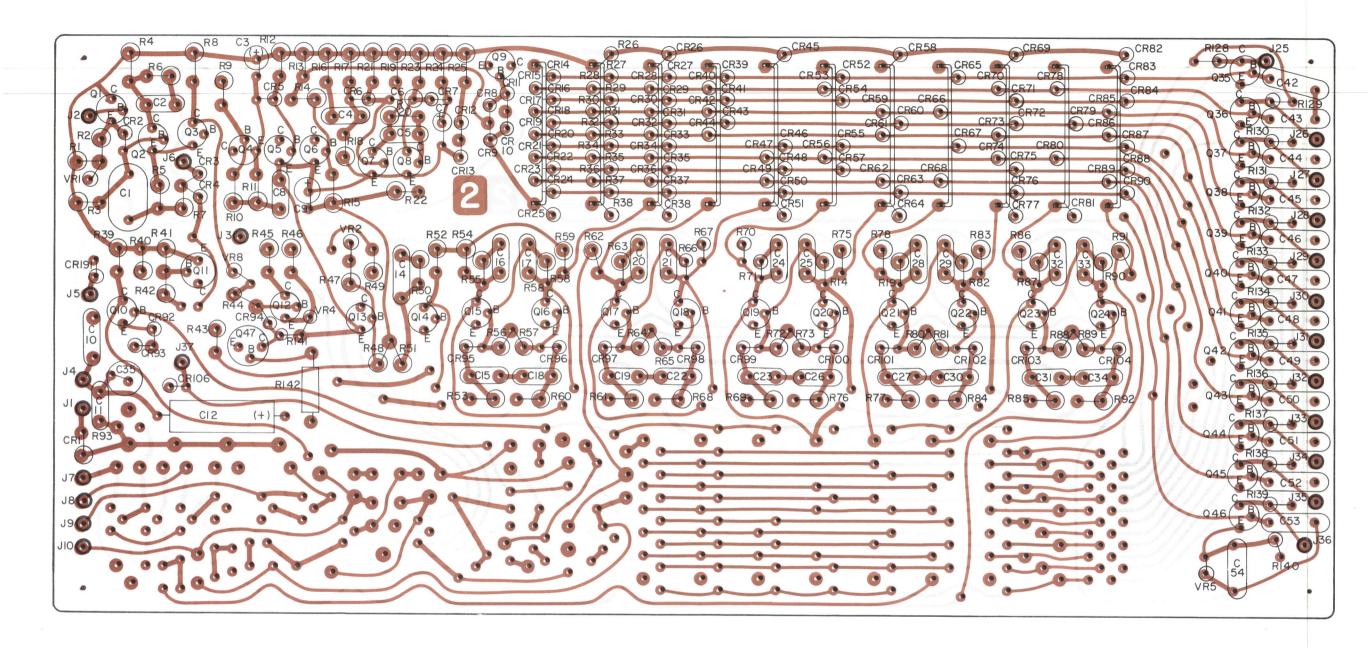
SYMBOL	G-E PART NO.	DESCRIPTION
C701	5496267- P 2	Tantalum: 47µf ±20%, 6VDCW; sim to Sprague Type 150D.
C702	5496267-P11	Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
C703 thru C706	5494481-P21	Ceramic disc: .01 μf $\pm 20\%$, 500 VDCW; sim to RMC Type JF Discap.
FL1	PL-19C304251-G1	
R701	3R77-P103J	Composition: 10,000 ohms $\pm 5\%$, 1/2 w.
R702	3R77-P510J	Composition: 51 ohms $\pm 5\%$, $1/2$ w.
R703	3R77-P242J	Composition: 2400 ohms $\pm 5\%$, $1/2$ w.
R704 thru R707	3R77-P102J	Composition: 1000 ohms ±5%, 1/2 w.
		TERMINAL BOARDS
TB1 and TB2	7775500-P24	Phen: 8 terminals.
TB3 and TB4	7775500- P 18	Phen: 8 terminals.
TB708	7117710-P5	Phen: 5 terminals; sim to Cinch 1775.
TB709 and TB710	7117710-P10	Phen: 10 terminals; sim to Cinch 1799.

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.



DECODER PANEL

17



(19D402881, Rev. 0) (19D402739, Sh. 1, Rev. 2) (19D402739, Sh. 2, Rev. 2)



OUTLINE DIAGRAM

LOGIC BOARD A2 DECODE ONLY

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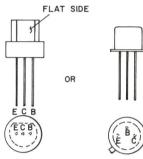


LEAD ORIENTATION FOR FOR CR26, CR45, CR58, CR59 & CR82

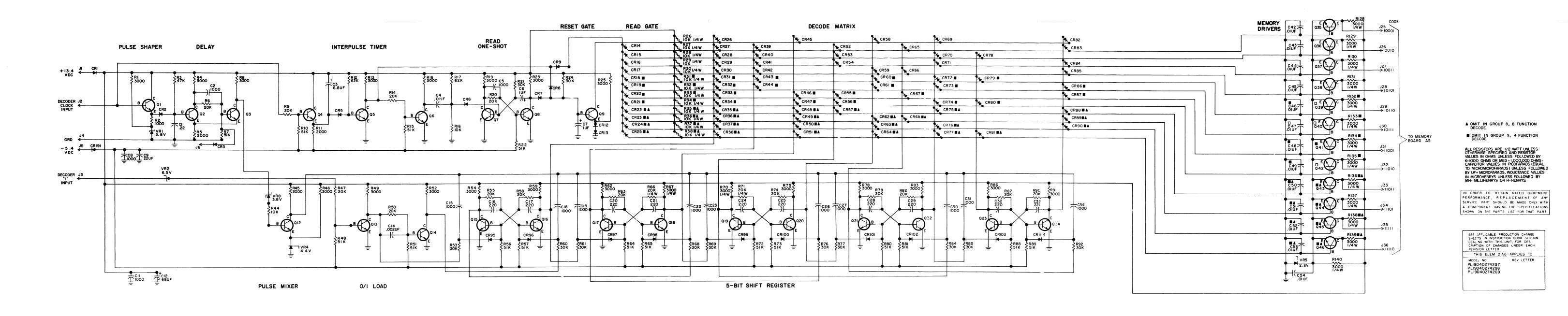


LEAD ORIENTATION FOR CR27 THRU CR44 CR46 THRU CR57 CR59 THRU CR68

CR46 THRU CR57 CR59 THRU CR68 CR70 THRU CR81 CR83 THRU CR90 CR14 THRU CR25



LEAD IDENTIFICATION FOR QI THRU Q47



(19R620772, Rev. 3)

SCHEMATIC DIAGRAM

LOGIC BOARD A2 DECODE ONLY

LBI-3819

PARTS LIST

LBI-3805

LOGIC BOARD - A2 DECODE PL-19D402742-G7 - 9

SYMBOL	G-E PART NO.	DESCRIPTION
		PL-19D402742-G7 12 Function PL-19D402742-G8 8 Function PL-19D402742-G9 4 Function
Cl	19B209243-P109	Polyester: 0.22 µf ±10%, 40 VDCW.
C2	5494481-P111	Ceramic disc: .001 μf $\pm 20\%,$ 1000 VDCW; sim to RMC Type JF Discap.
C3	5496267-P218	Tantalum: 6.8 μ f \pm 10%, 35 VDCW; sim to Sprague Type 150D.
C4	5491189-P201	Polyester: .01 µf ±5%, 50 VDCW.
C5	5494481-P111	Ceramic disc: .001 μf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C6 and C7	5496267-P217	Tantalum: 1.0 μf ±10%, 35 VDCW; sim to Sprague Type 150D.
C8	5494481-P111	Ceramic disc: .001 μf $\pm 20\%,$ 1000 VDCW; sim to RMC Type JF Discap.
C9	5496267-P10	Tantalum: $22 \mu f \pm 20\%$, 15 VDCW; sim to Sprague Type 150D.
C11	5494481-P111	Ceramic disc: .001 μf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C12	5496267-P11	Tantalum: 68 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D.
C14	5494481-P113	Ceramic disc: .002 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C15	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C16 and C17	5494481-P103	Ceramic disc: 220 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap.
C18 and C19	5494481-P111	Ceramic disc: .001 μf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C20 and C21	5494481-P103	Ceramic disc: 220 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap.
C22 and C23	5494481-P111	Ceramic disc: .001 μf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C24 and C25	5494481-P103	Ceramic disc: 220 pf \pm 20%, 1000 VDCW; sim to RMC Type JF Discap.
C26 and C27	5494481-P111	Ceramic disc: .001 μf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C28 and C29	5494481-P103	Ceramic disc: 220 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C30 and C31	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C32 and C33	5494481-P103	Ceramic disc: 220 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C34	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C42 thru C45	19B209243-P1	Polyester: .01 µf ±20%, 40 VDCW.
C46 thru C49	19B209243-P1	Polyester: .01 µf ±20%, 40 VDCW. (Used in 8 and 12 Function only).
C50 thru C53	19B209243-P1	Polyester: .01 µf ±20%, 40 VDCW. (Used in 12 Function only).
C54	19B209243-P1	Polyester: .01 µf ±20%, 40 VDCW.

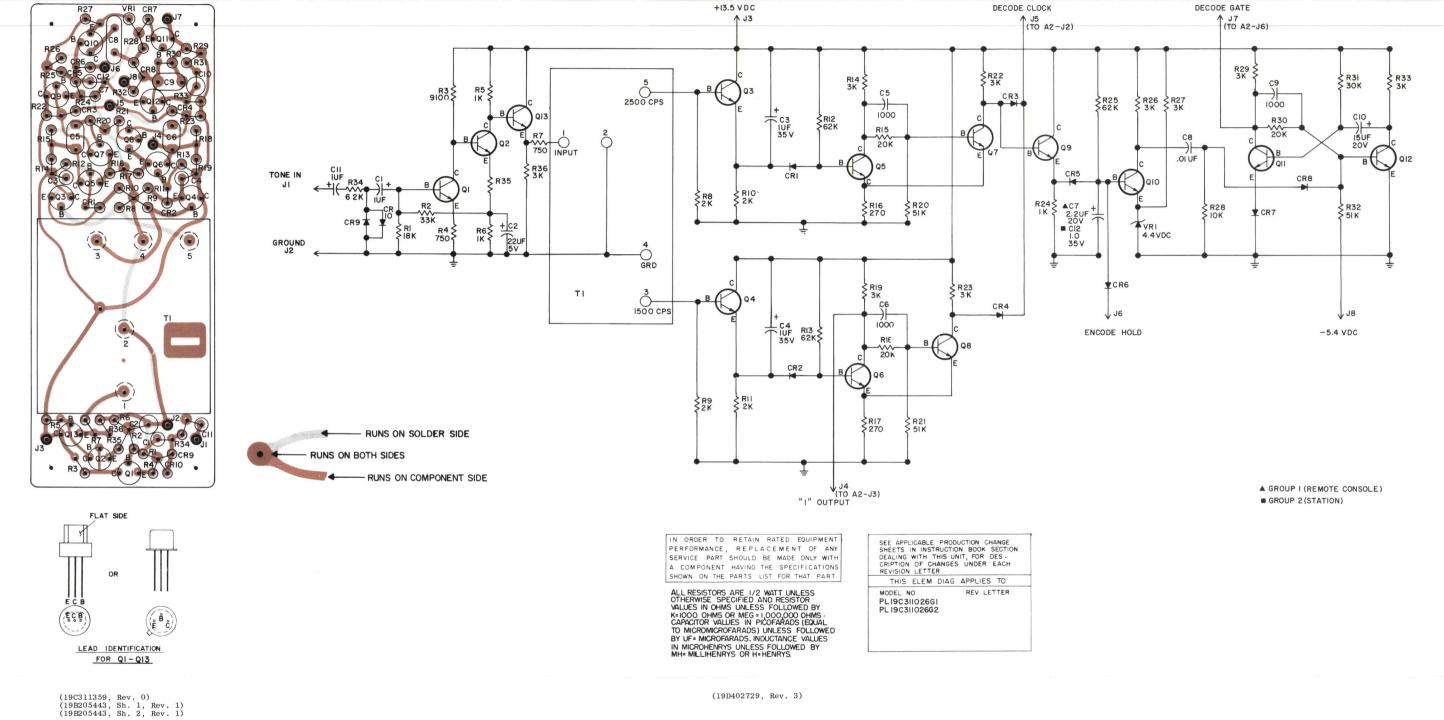
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SYMBOL	G-E PART NO	DESCRIPTION	SYMBOL	G-E PART NO	DESCRIPTION	SYMBOI	G-E PART NO	DESCRIPTION
CR1	4037822-P1	DIODES AND RECTIFIERS	CR88 thru CR90	19A115250-P1	Silicon. (Used in 12 Function only).	R31 thru R34	3R77-P103J	Composition: 10,000 ohms ±5%, 1/2 w. (Used in 8 and 12 Function only).
CR2 and CR3	19A115250-P1	Silicon.	CR95 thru CR104	19A115250-P1	Silicon.	R35 thru R38	3R77-P103J	Composition: 10,000 ohms ±5%, 1/2 w. (Used in 12 Function only).
CR5	19A115250-P1	Silicon.	CR191	19A115250-P1	Silicon.	R44	3R77-P103J	Composition: 10,000 ohms ±5%, 1/2 w.
thru CR9			VRl	4036887-P3	Silicon, Zener®.	R45	3R77-P202J	Composition: 2000 ohms ±5%, 1/2 w.
CR12	19A115250-P1	Silicon.	VR2	4036887-P6	Silicon, Zener⊕.	R46	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
thru CR17			VR4	4036887-P4	Silicon, Zener⊕.	R47	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR18	19A115250-P1	Silicon.	VR5	4036887-P2	Silicon, Zener⊕.	R48	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
thru CR21		(Used in 8 and 12 Function only).	VR8	4036887-P3	Silicon, Zener®.	R49	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR22 thru	19A115250-P1	Silicon.				R50	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR25		(Used in 12 Function only).	l		JACKS AND RECEPTACLES	R51	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
CR26 thru	19A115250-P1	Silicon.	J1 thru	4033513-P15	Contact, electrical: sim to Bead Chain R40-1A.	R52	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR30			J37			R53	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
CR31 thru	19A115250-P1	Silicon. (Used in 8 and 12 Function only).			TRANSISTORS	R54	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR34		(Used in 8 and 12 Function only).	Q1	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	R55	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR35	19A115250-P1	Silicon.	thru Q9			R56	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
thru CR38		(Used in 12 Function only).	Q12	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	and R57		
CR39	19A115250-P1	Silicon.	thru Q24			R58	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
thru CR42			Q35	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	R59	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR43	19A115250-P1	Silicon.	thru Q38	Ì		R60	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
and CR44		(Used in 8 and 12 Function only).	Q39	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	and R61	1	
CR45	19A115250-P1	Silicon.	thru Q42		(Used in 8 and 12 Function only),	R62	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR46	19A115250-P1	Silicon.	Q43	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	R63	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
and CR47		(Used in 8 and 12 Function only).	thru Q46		(Used in 12 Function only).	R64	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
CR48	19A115250-P1	Silicon.				and R65		
thru CR51		(Used in 12 Function only).			RESISTORS	R66	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR52	19A115250-P1	Silicon.	R1	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	R67	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
thru CR54			R2	3R77-P102J	Composition: 1000 ohms ±5%, 1/2 w.	R68	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
CR55	19A115250-P1	Silicon.	R3	3R77-P473J	Composition: 47,000 ohms ±5%, 1/2 w.	and R69		
and CR56		(Used in 8 and 12 Function only).	R4	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	R70	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR57	19A115250-P1	Silicon. (Used in 12 Function only).	R5	3R77-P202J	Composition: 2000 ohms ±5%, 1/2 w.	R71	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR58	19A115250-P1	Silicon.	R6	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.	R72	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
and CR59			R7	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.	and R73		
CR60	19A115250-P1	Silicon.	R8	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	R74	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
and CR61	İ	(Used in 8 and 12 Function only).	R9	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.	R75	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR62	19A115250-P1	Silicon.	R10	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.	R76	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
thru CR64		(Used in 12 Function only).	R11	3R77-P432J	Composition: 4300 ohms ±5%, 1/2 w.	and R77		
CR65	19A115250-P1	Silicon.	R12	3R77-P623J	Composition: 62,000 ohms ±5%, 1/2 w.	R78	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
and CR66			R13	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	R79	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR67	19A115250-P1	Silicon. (Used in 8 and 12 Function only).	R14	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.	R80	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
CR68	19A115250-P1	Silicon. (Used in 12 Function only).	R15	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.	and R81		
CR69	19A115250-P1	Silicon.	R16	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	R82	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
thru CR71			R17	3R77-P623J	Composition: 62,000 ohms ±5%, 1/2 w.	R83	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
CR72	19A115250-P1	Silicon.	R18	3R77-P103J	Composition: 10,000 ohms ±5%, 1/2 w.	R84	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
thru CR74		(Used in 8 and 12 Function only).	R19	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	and R85		, , , , , , , , ,
CR75	19A115250-P1	Silicon.	R20	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.	R86	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
thru CR77	1	(Used in 12 Function only).	R21	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.	R87	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR78	19A115250-P1	Silicon.	R22	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.	R88	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
CR79	19A115250-P1	Silicon.	R23	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	and R89		
and CR80	ĺ	(Used in 8 and 12 Function only).	R24	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.	R90	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
CR81	19A115250-P1	Silicon. (Used in 12 Function only).	R25	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	R91	3R77-P302J	Composition: 3000 ohms 15%, 1/2 w.
CR82	19A115250-P1	Silicon.	R26 thru	3R77-P103J	Composition: 10,000 ohms ±5%, 1/2 w.	R92	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
thru CR85			R30				1	
CR86	19A115250-P1	Silicon.						
and CR87		(Used in 8 and 12 Function only).						
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SYMBOL	G-E PART NO	DESCRIPTION
R128 thru R131	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
R132 thru R135	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w. (Used in 8 and 12 Function only).
R136 thru R139	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w. (Used in 12 Function only).
R140	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
	:	
		1

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

OUTLINE DIAGRAM

SCHEMATIC DIAGRAM



SCHEMATIC & OUTLINE DIAGRAM

TONE DISCRIMINATOR A7

LBI-3819

PARTS LIST

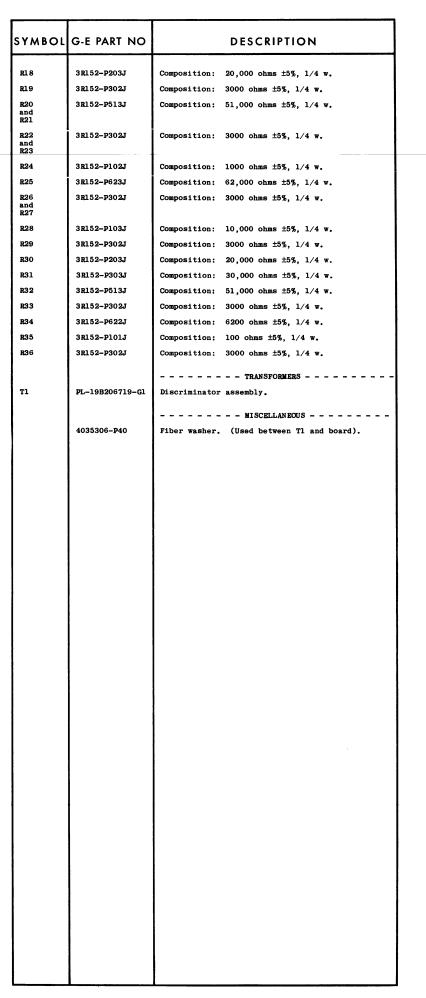
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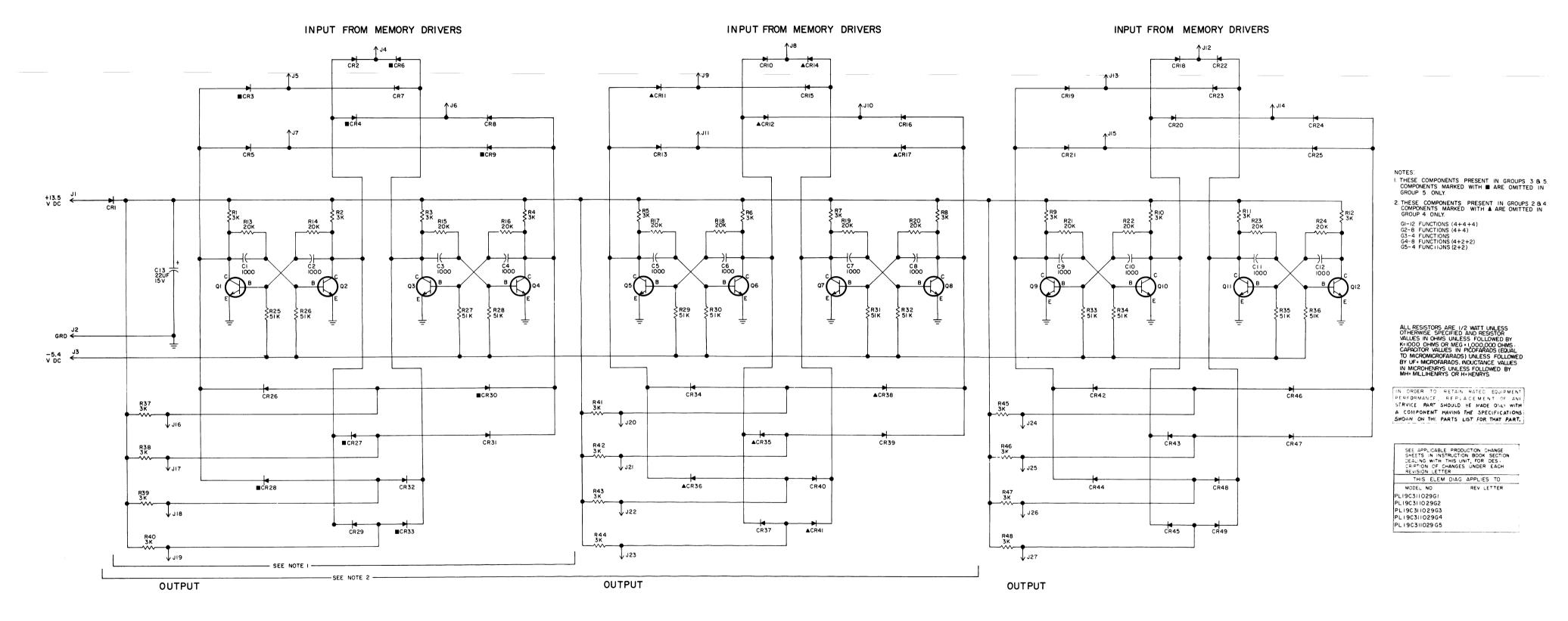
TONE DISCRIMINATOR - A7 PL-19C311026-G1-2

SYMBOL	G-E PART NO.	DESCRIPTION
		PL-19C311026-G1 Console PL-19C311026-G2 Station Panel
		CAPACITORS
Cl	5496267-P17	Tantalum: 1.0 μf ±20%, 35 VDCW; sim to Sprague Type 150D.
C2	5496267-P10	Tantalum: 22 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D.
C3 and C4	5496267-P17	Tantalum: 1.0 μf $\pm 20\%$, 35 VDCW; sim to Sprague Type 150D.
C5 and C6	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C7	5496267-P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. (Used in PL-19C311026-G1).
C8	19B209243-P101	Polyester: .01 µf ±10%, 40 VDCW.
C9	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C10	5496267-P214	Tantalum: 15 μ f \pm 10%, 20 VDCW; sim to Sprague Type 150D.
C11	5496267-P17	Tantalum: 1.0 μ f $\pm 20\%$, 35 VDCW; sim to Sprague Type 150D.
C12	5496267-P217	Tantalum: 1.0 μ f \pm 10%, 35 VDCW; sim to Sprague Type 150D. (Used in PL-19C311026-G2).
		DIODES AND RECTIFIERS
CR1 thru	19A115250-P1	Silicon.
CR10 VR1	4036887-P4	Silicon, Zener.
J1 thru J8	4033513-P15	Contact, electrical: sim to Bead Chain R40-1A.
Q1 thru Q13	19A115123-P1	TRANSISTORS
		RESISTORS
R1	3R152-P183J	Composition: 18,000 ohms ±5%, 1/4 w.
R2	3R152-P333J	Composition: 33,000 ohms ±5%, 1/4 w.
R3	3R152-P912J	Composition: 9100 ohms ±5%, 1/4 w.
R4	3R152-P751J	Composition: 750 ohms $\pm 5\%$, $1/4$ w.
R5 and R6	3R152-P102J	Composition: 1000 ohms $\pm 5\%$, $1/4$ w.
R7	3R152-P751J	Composition: 750 ohms ±5%, 1/4 w.
R8 thru	3R152-P202J	Composition: 2000 ohms ±5%, 1/4 w.
R11 R12 and	3R152-P623J	Composition: 62,000 ohms ±5%, 1/4 w.
R13	00150 -000-	
R14	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
R15 R16 and	3R152-P203J 3R152-P271J	Composition: 20,000 ohms ±5%, 1/4 w. Composition: 270 ohms ±5%, 1/4 w.
R17		

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*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.



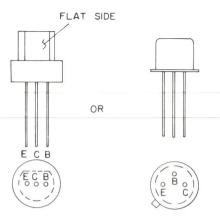


(19R620766, Rev. 1)

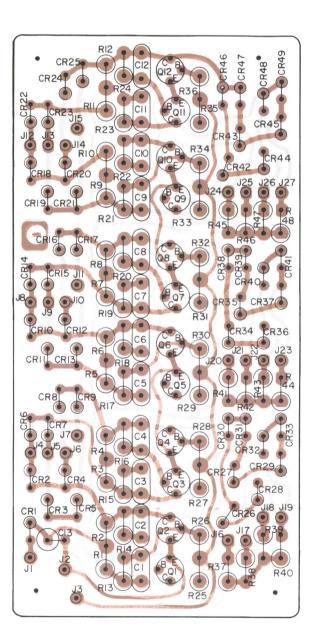
SCHEMATIC DIAGRAM

MEMORY BOARD A5

Issue 1 23



LEAD IDENTIFICATION
FOR Q1 THRU Q12



(19C311358, Rev. 0) (19B205444, Sh. 1, Rev. 0) (19B205444, Sh. 2, Rev. 0)

OUTLINE DIAGRAM

RUNS ON SOLDER SIDE

RUNS ON COMPONENT SIDE

- RUNS ON BOTH SIDES

MEMORY BOARD A5

4 Issue 1

PARTS LIST

LBI-3806

MEMORY BOARD - A5 PL-19C311029-G1-5

	,1	PL-19C311029-G1-5	CR41	19A115250-PI	Silicon. (
			CR42 thru CR49	19Al15250-P1	Silicon. (
SYMBOL	G-E PART NO.	DESCRIPTION			
		PL-19C311029-G1 12 Functions (4 + 4 + 4) PL-19C311029-G2 8 Functions (4 + 4) PL-19C311029-G3 4 Functions PL-19C311029-G4 8 Functions (4 + 2 + 2)	J1 thru J27	4033513-P15	Contact, el
		PL-19C311029-G5 4 Functions (2 + 2)	Q1 thru Q4	19All5123-Pl	Silicon, NI
C1 thru C4	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	Q5 thru Q8	19Al15123-P1	Silicon, NI (Used in PI
C5 thru C8	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap. (Used in PL-19C311029-GI, 2 and 4).	Q9 thru Q12	19All5123-P1	Silicon, NI (Used in PI
C9 thru C12	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap. (Used in PL-19C311029-G1).			
C13	5496267-P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	thru R4	3R77-P302J	Composition
ana	104115050 71	DIODES AND RECTIFIERS	R5 thru R8	3R77-P302J	Composition (Used in PL
CR1 and CR2	19A115250-P1	Silicon.	R9 thru R12	3R77-P302J	Composition (Used in PL
CR3 and CR4	19A115250-P1	Silicon. (Used in PL-19C311029-G1-4).	R13 thru R16	3R77-P203J	Composition
CR5	19A115250-P1	Silicon.	R17	3R77-P203J	Composition
R6	19A115250-P1	Silicon. (Used in PL-19C311029-G1-4).	thru R20		(Used in PL
R7 nd R8	19A115250-P1	Silicon.	R21 thru R24	3R77-P203J	Composition (Used in PL
R9	19A115250-P1	Silicon. (Used in PL-19C311029-G1-4).	R25	3R77-P513J	Composition
10	19A115250-P1	Silicon. (Used in PL-19C311029-Gl, 2 and 4).	thru R28		
l1 i l2	19A115250-P1	Silicon. (Used in PL-19C311029-Gl and 2).	R29 thru R32	3R77-P513J	Composition (Used in PL
13	19A115250-P1	Silicon. (Used in PL-19C311029-G1, 2 and 4).	R33	3R77-P513J	Composition
14	19A115250-P1	Silicon. (Used in PL-19C311029-G1 and 2).	thru R36		(Used in PL
15 d 16	19A115250-P1	Silicon. (Used in PL-19C311029-G1, 2 and 4).	R37 thru R40	3R77-P302J	Composition
R17	19A115250-P1	Silicon. (Used in PL-19C311029-Gl and 2).	R41	3R77-P302J	Composition
R18 1ru R25	19A115250-P1	Silicon. (Used in PL-19C311029-G1).	thru R44	000000000000000000000000000000000000000	(Used in PL
R26	19A115250-P1	Silicon.	R45 thru R48	3R77-P302J	Composition (Used in PL
R27 id R28	19A115250-P1	Silicon. (Used in PL-19C311029-G1-4).			
CR29	19A115250-P1	Silicon.			
R30	19A115250-P1	Silicon. (Used in PL-19C311029-G1-4).			
R31 nd R32	19A115250-P1	Silicon.			
CR33	19A115250-P1	Silicon. (Used in PL-19C311029-G1-4).			
R34	19A115250-P1	Silicon. (Used in PL-19C311029-G1, 2 and 4).			
R35 nd R36	19A115250-P1	Silicon. (Used in PL-19C311029-Gl and 2).			
R37	19Al15250-P1	Silicon. (Used in PL-19C311029-G1, 2 and 4).			
CR38	19A115250-P1	Silicon. (Used in PL-19C311029-Gl and 2).			

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

CR39 and CR40 CR41 CR42 thru CR49 J1 thru Q4 Q5 thru Q4 Q5 thru Q8 Q9 thru Q12 R1 thru R4 R5 R5 R1 R7 thru R1 R1 R1 R2 R1 R1 R2 R2 R1 R1 R2 R1 R2 R1 R2 R2 R1 R2 R2 R1 R2 R2 R1 R2 R2 R2 R1 R2	19A115250-P1 19A115250-P1 19A115250-P1 19A115123-P1 19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J 3R77-P203J	Silicon. (Used in PL-19C311029-Gl, 2 and 4). Silicon. (Used in PL-19C311029-Gl and 2). Silicon. (Used in PL-19C311029-Gl).
CR42 thru CR49 J1 thru J27 Q1 thru Q4 thru Q8 Q9 thru Q8 thru R1 thru R8 R1 thru R8 R1 thru R1 R1 R1 R1 R1 R1 R1 R2 R2 R2 R2 R2 R25 R25 R25	19A115250-P1 4033513-P15 19A115123-P1 19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J 3R77-P302J	Silicon. (Used in PL-19C311029-G1). JACKS AND RECEPTACLES Contact, electrical: sim to Bead Chain R40-1A. TRANSISTORS Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1). RESISTORS Composition: 3000 ohms ±5%, 1/2 w. Composition: 3000 ohms ±5%, 1/2 w. Composition: 3000 ohms ±5%, 1/2 w.
thru CR49 J1 thru J27 Q1 thru Q4 Q5 thru Q8 thru Q12 R1 thru R8 R9 thru R1 thru R1	4033513-P15 19A115123-P1 19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
J1 thru J27 Q1 thru Q4 Q5 thru Q8 Q9 thru Q12 R1 thru R4 R5 thru R8 R9 thru R1 thru R1	19A115123-P1 19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Contact, electrical: sim to Bead Chain R40-1A. TRANSISTORS Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1). RESISTORS
thru J27 Q1 thru Q4 Q5 thru Q8 Q9 thru Q12 R1 R1 R4 R5 thru R8 R9 thru R12 R13 R17 thru R16 R17 thru R20 R21 R24 R25 R25 R21 R24 R25 R25 R25 R27	19A115123-P1 19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Contact, electrical: sim to Bead Chain R40-1A. TRANSISTORS Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1). RESISTORS
thru J27 Q1 thru Q4 Q5 thru Q8 Q9 thru Q12 R1 R1 R4 R5 thru R8 R9 thru R12 R13 R17 thru R16 R17 thru R20 R21 R24 R25 R25 R21 R24 R25 R25 R25 R27	19A115123-P1 19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1).
Q1 thru Q4 Q5 thru Q8 Q9 thru Q12 R1 thru R4 R5 thru R1 thru R1	19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1).
thru Q4 Q5 thru Q8 Q9 thru Q1 R1 thru R4 R5 thru R8 R9 thru R1	19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1).
thru Q4 Q5 thru Q8 Q9 thru Q1 R1 thru R4 R5 thru R8 R9 thru R1	19A115123-P1 19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-GI, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-GI).
Q5 thru Q8 Q9 thru Q12 R1 thru R4 R5 thru R1 R1 R1 R7 thru R1	19A115123-P1 3R77-P302J 3R77-P302J 3R77-P302J	(Used in PL-19C311029-G1, 2 and 4). Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1).
Q9 thru Q12 R1 thru R5 thru R8 R9 thru R1.2 R1.3 thru R1.6 R1.7 thru R2.0 R2.1 thru R2.4	3R77-P302J 3R77-P302J 3R77-P302J 3R77-P203J	Silicon, NPN; sim to Type 2N2712. (Used in PL-19C311029-G1).
RI thru RS thru R8 R9 thru R12 R13 thru R12 R13 thru R14 R17 thru R24 R25 thru	3R77-P302J 3R77-P302J 3R77-P302J 3R77-P203J	(Used in PL-19C311029-G1).
thru R4 R5 thru R8 R9 thru R12 R13 thru R1.6 R1.7 R20 R21 thru R24 R25 thru	3R77-P302J 3R77-P302J 3R77-P203J	Composition: 3000 ohms ±5%, 1/2 w. Composition: 3000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1, 2 and 4). Composition: 3000 ohms ±5%, 1/2 w.
thru R4 R5 thru R8 R9 thru R12 R13 thru R1.6 R1.7 R20 R21 thru R24 R25 thru	3R77-P302J 3R77-P302J 3R77-P203J	Composition: 3000 ohms ±5%, 1/2 w. Composition: 3000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1, 2 and 4). Composition: 3000 ohms ±5%, 1/2 w.
R4 R5 thru R8 R9 thru R12 R13 thru R16 R17 thru R20 R21 thru R24 R25 thru	3R77-P302J 3R77-P302J 3R77-P203J	Composition: 3000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1, 2 and 4). Composition: 3000 ohms ±5%, 1/2 w.
thru R8 R9 R9 R12 R13 thru R16 R17 thru R20 R21 thru R20 R21 thru R24 R25 thru	3R77-P302J 3R77-P203J	(Used in PL-19C311029-G1, 2 and 4). Composition: 3000 ohms ±5%, 1/2 w.
thru R12 R13 thru R16 R17 thru R20 R21 thru R24 R25	3R77-P203J	Composition: 3000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1).
R13 thru R16 R17 thru R20 R21 thru R24		
R17 thru R20 R21 thru R24 R25 thru	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
R21 thru R24 R25 thru	1	Composition: 20,000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1, 2 and 4).
R25 thru	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w. (Used in PL-19C3i1029-G1).
1,20	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w.
R29 thru R32	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1, 2 and 4).
R33 thru R36	3R77-P513J	Composition: 51,000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1).
R37 thru R40	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
R41 thru R44	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1, 2 and 4).
R45 thru R48	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w. (Used in PL-19C311029-G1).

PARTS LIST

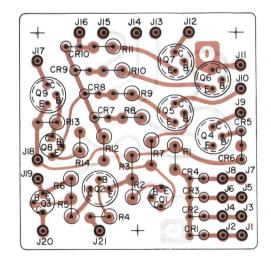
TRANSMITTER - RECEIVER SWITCHING - A3 PL-19B205497-G1

SYMBOL	G-E PART NO.	DESCRIPTION
CR1 thru CR10	19A115250-P1	DIODES AND RECTIFIERS
J1 thru J21	4033513-P15	JACKS AND RECEPTACLES
		TRANSISTORS
Q1	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q2	19A115706-P1	Silicon, PNP; sim to Type 2N3638.
Q3	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q4 thru Q7	19A115706-P1	Silicon, PNP; sim to Type 2N3638.
Q8	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q9	19A115706-P1	Silicon, PNP; sim to Type 2N3638.
		·
R1	3R77-P224J	Composition: 0.22 megohm ±5%, 1/2 w.
R2	3R77-P242J	Composition: 2400 ohms ±5%, 1/2 w.
R3	3R77-P512J	Composition: 5100 ohms $\pm 5\%$, $1/2$ w.
R4	3R77-P433J	Composition: $43,000$ ohms $\pm 5\%$, $1/2$ w.
R5	3R77-P163J	Composition: $16,000$ ohms $\pm 5\%$, $1/2$ w.
R6	3R77-P103J	Composition: $10,000$ ohms $\pm 5\%$, $1/2$ w.
R7	3R77-P512J	Composition: 5100 ohms ±5%, 1/2 w.
R8 thru R11	3R77-P511J	Composition: 510 ohms ±5%, 1/2 w.
R12	3R77-P203J	Composition: 20,000 ohms ±5%, 1/2 w.
R13	3R77-P153J	Composition: 15,000 ohms $\pm 5\%$, $1/2$ w.
R14	3R77-P751J	Composition: 750 ohms ±5%, 1/2 w.
		MISCELLANEOUS
	4036555-P1	Insulator, washer: nylon. (Used with Q2, Q4, Q5, Q6, Q7 and Q9).

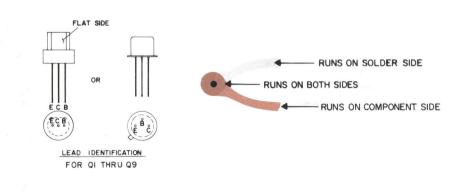
RCVR
FI

CR2
CR3
CR7
CR5
C

OUTLINE DIAGRAM



(19B205892, Rev. 0) (19B205496, Sh. 1, Rev. 0) (19B205496, Sh. 2, Rev. 0)



SCHEMATIC & OUTLINE DIAGRAM

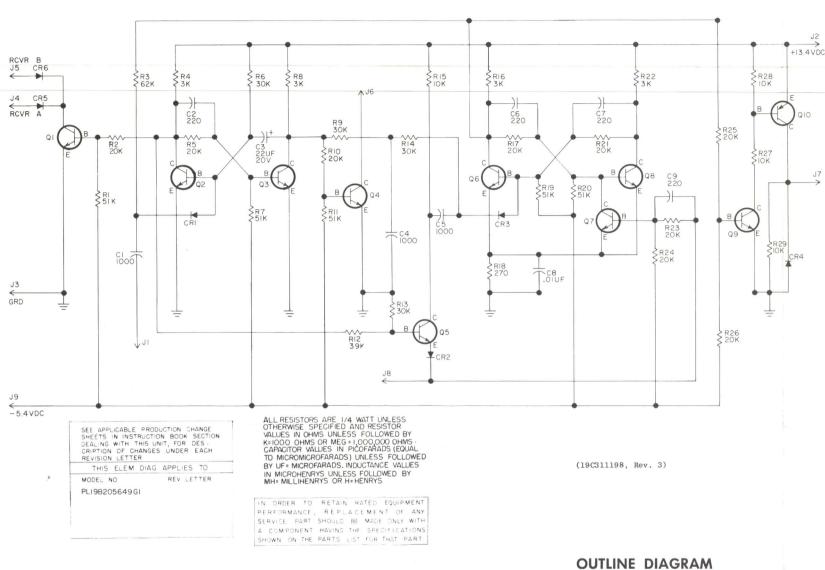
TRANSMITTER-RECEIVER SWITCHING BOARD A3

LBI-3821

TIMING BOARD - A8 PL-19B205649-G1

STMBOL	G-E PART NO.	DESCRIPTION
C1	5494481-P111	Ceramic disc: .001 μf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C2	5494481-P103	Ceramic disc: 220 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C3	5496267-P10	Tantalum: 22 μ f \pm 20%, 15 VDCW; sim to Sprague Type 150D.
C4 and C5	5494481-P111	Ceramic disc: .001 μf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C6 and C7	5494481-P103	Ceramic disc: 220 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C8	19B209243-P101	Polyester: .01 µf ±10%, 40 VDCW.
C9	5494481-P103	Ceramic disc: 220 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
		DIODES AND RECTIFIERS
CR1 thru CR6	19A115250-P1	Silicon.
		TRANSISTORS
Q1 thru Q9	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q10	19Al15768-Pl	Silicon, PNP; sim to Type 2N3702.
R1	3R152-P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R2	3R152-P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R3	3R152-P623J	Composition: 62,000 ohms ±5%, 1/4 w.
R4	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
R5	3R152-P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R6	3R152-P303J	Composition: 30,000 ohms ±5%, 1/4 w.
R7	3R152-P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R8	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
R9	3R152-P303J	Composition: 30,000 ohms ±5%, 1/4 w.
R10	3R152-P202J	Composition: 20,000 ohms ±5%, 1/4 w.
R11	3R152-P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R12	3R152-P393J	Composition: 39,000 ohms ±5%, 1/4 w.
R13 and R14	3R152-P303J	Composition: 30,000 ohms ±5%, 1/4 w.
R15	3R152-P103J	Composition: 10,000 ohms ±5%, 1/4 w.
R16	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
R17	3R152-P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R18	3R152-P271J	Composition: 270 ohms ±5%, 1/4 w.
R19 and R20	3R152-P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R21	3R152-P203J	Composition: 20,000 ohms $\pm 5\%$, $1/4$ w.
R22	3R152-P302J	Composition: 3000 ohms ±5%, 1/4 w.
R23 thru R26	3R152-P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R27 thru R29	3R152-P103J	Composition: 10,000 ohms ±5%, 1/4 w.
je.		

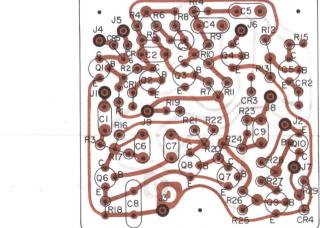
*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

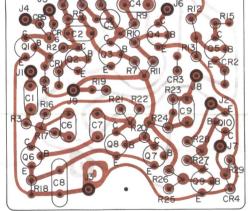


FLAT SIDE

LEAD IDENTIFICATION FOR QI THRU QIO

ECB







SCHEMATIC & OUTLINE DIAGRAM

RUNS ON BOTH SIDES

- RUNS ON SOLDER SIDE

RUNS ON COMPONENT SIDE

TIMING BOARD A8

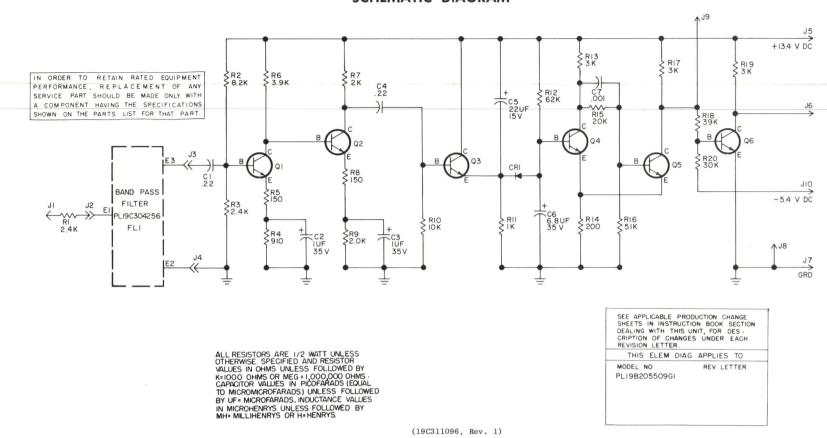
26 Issue 1 LBI-3820

3-KC DETECTOR - A6 PL-19B205509-G1

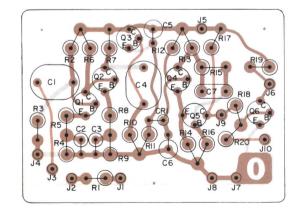
SYMBOL	G-E PART NO.	DESCRIPTION
		CAPACITORS
C1	19B209243-P9	Polyester: 0.22 μf ±20%, 40 VDCW.
C2	5496267-P217	Tantalum: 1.0 µf ±10%, 35 VDCW; sim
and C3		to Sprague Type 150D.
C4	19B209243-P9	Polyester: 0.22 µf ±20%, 40 VDCW.
C5	5496267-P210	Tantalum: 22 µf ±10%, 15 VDCW; sim to Sprague Type 150D.
C6	5496267-P218	Tantalum: 6.8 μf ±10%, 35 VDCW; sim
C7	5494481-P111	to Sprague Type 150D. Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to
		RMC Type JF Discap.
		DIODES AND RECTIFIERS
CR1	19A115250-P1	Silicon.
		JACKS AND RECEPTACLES
J1 thru	4033513-P15	Contact, electrical: sim to Bead Chain R40-1A.
J10		
		TRANSISTORS
Q1	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
thru Q6		
		RESISTORS
R1	3R77-P242J	Composition: 2400 ohms ±5%, 1/2 w.
R2	3R77-P822J	Composition: 8200 ohms ±5%, 1/2 w.
R3	3R77-P242J	Composition: 2400 ohms ±5%, 1/2 w.
R4	3R77-P911K 3R77-P151K	Composition: 910 ohms ±10%, 1/2 w.
R5 R6	3R77-P392K	Composition: 150 ohms ±10%, 1/2 w. Composition: 3900 ohms ±10%, 1/2 w.
R7	3R77-P202K	Composition: 2000 ohms ±10%, 1/2 w.
R8	3R77-P151K	Composition: 150 ohms ±10%, 1/2 w.
R9	3R77-P202K	Composition: 2000 ohms ±10%, 1/2 w.
RlO	3R77-P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R11	3R77-P102K	Composition: 1000 ohms ±10%, 1/2 w.
R12	3R77-P623K	Composition: 62,000 ohms ±10%, 1/2 w.
R13	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
R14	3R77-P201J	Composition: 200 ohms ±5%, 1/2 w.
R15	3R77-P203K	Composition: 20,000 ohms $\pm 10\%$, $1/2$ w.
R16	3R77-P513K	Composition: 51,000 ohms ±10%, 1/2 w.
R17	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
R18	3R77-P393J	Composition: 39,000 ohms ±5%, 1/2 w.
R19	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.
R20	3R77-P303J	Composition: 30,000 ohms ±5%, 1/2 w.
	-	

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

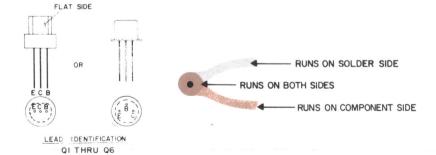
SCHEMATIC DIAGRAM



OUTLINE DIAGRAM



(19B205885, Rev. 0) (19B205508, Sh. 1, Rev. 0) (19B205508, Sh. 2, Rev. 0)

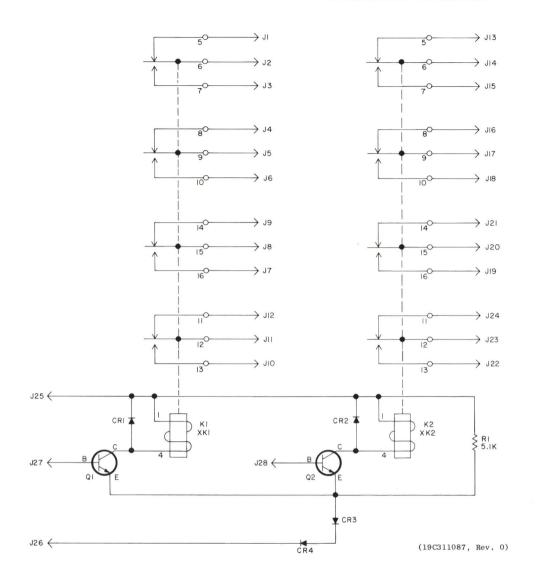


SCHEMATIC & OUTLINE DIAGRAM

3-KC DETECTOR A8

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SCHEMATIC DIAGRAM



ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY WEIGHT OF THE STREET OF THE

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS. LIST FOR THAT PART.

SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DES-CRIPTION OF CHANGES UNDER EACH REVISION LETTER.

THIS ELEM DIAG APPLIES TO MODEL NO PL19B205495G1

OUTLINE DIAGRAM

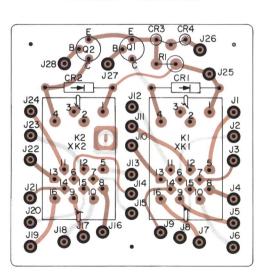


SCHEMATIC & OUTLINE DIAGRAM

Issue 1

RELAY CONTROL BOARD A4

28



(19B205893, Rev. 0) (19B205494, Sh. 1, Rev. 0) (19B205494, Sh. 2, Rev. 0)

PARTS LIST

LBI-3823

RELAY CONTROL - A4 PL-19A122460-G3

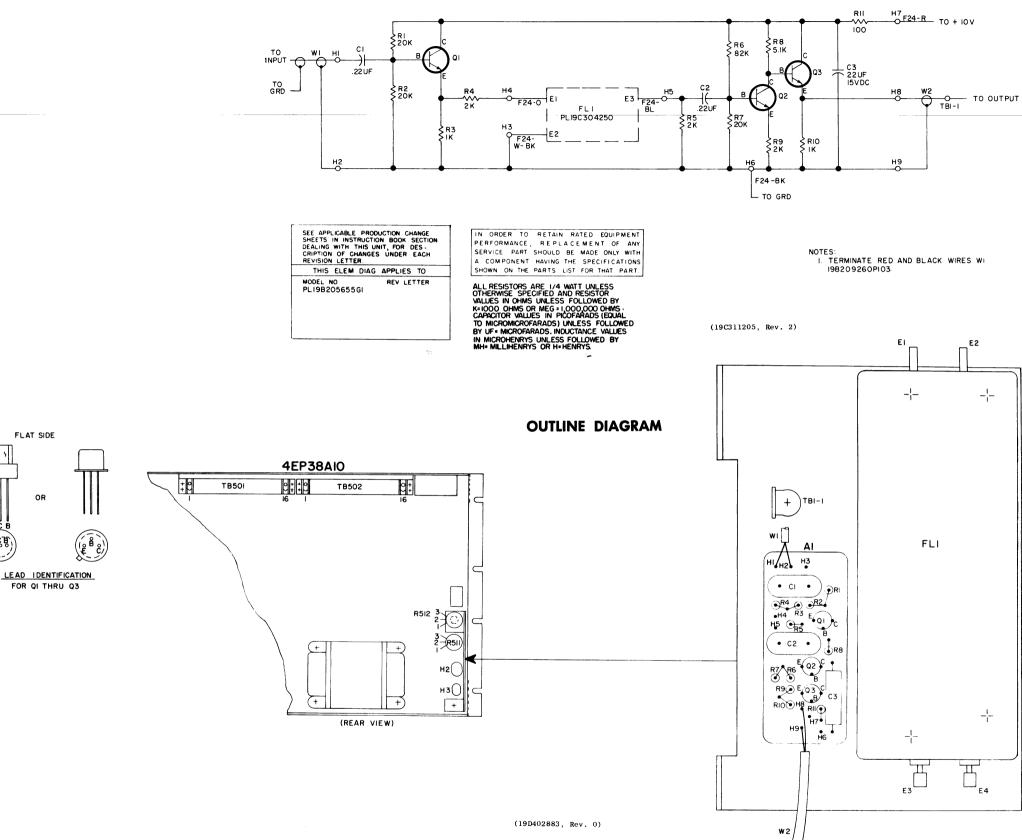
SYMBOL	G-E PART NO.	DESCRIPTION
		COMPONENT BOARD PL-19B205495-G1
CR1 thru CR4	19All5250-Pl	DIODES AND RECTIFIERS
J1 thru J28	4033513-P15	JACKS AND RECEPTACLES Contact, electrical: sim to Bead Chain R40-1A.
K1 and K2	5491595-P14	Armature: 1.5 w operating, 520 ohms ±15% coil res 4 form C contacts; sim to Allied Control T154-X-131.
Q1 and Q2	19All5123-Pl	TRANSISTORS
Rl	3R77-P512K	Composition: 5100 ohms ±10%, 1/2 w.
XK1 and XK2	5491595-P7	Relay: 10 contacts; sim to Allied Control 30054-4.
	5491595- P 9	Retainer: sim to Allied Control 30040-2. (Used with Kl and K2).
		HARNESS ASSEMBLY PL-19A122452-G1
	4036634-P1	Contact, electrical; sim to AMP 42428-2.

^{*}COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

LBI-3829

POWER SUPPLY MODIFICATION KIT PL-19A122460-Gl and G5

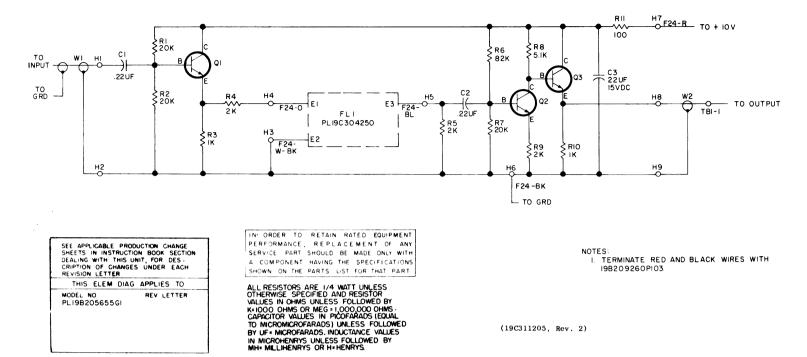
SYMBOL	G-E PART NO.	DESCRIPTION
		FILTER ASSEMBLY PL-19B205663-G1
Al		COMPONENT BOARD
		PL-19B205665-G1
C1 and C2	19B209243-P15	Polyester: 0.22 μf ±20%, 250 VDCW.
сз	5496267-P10	Tantalum: 22 μf $\pm 20\%$, 15 VDCW; sim to Sprague Type 150D.
Q1 thru Q3	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
R1 and R2	3R152-P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R3	3R152-P102J	Composition: 1000 ohms $\pm 5\%$, $1/4$ w.
R4 and R5	3R152-P202J	Composition: 2000 ohms ±5%, 1/4 w.
R6	3R152-P823J	Composition: 82,000 ohms $\pm 5\%$, $1/4$ w.
R7	3R152-P203J	Composition: 20,000 ohms $\pm 5\%$, $1/4$ w.
R8	3R152-P512J	Composition: 5100 ohms $\pm 5\%$, $1/4$ w.
R9	3R152-P202J	Composition: 2000 ohms ±5%, 1/4 w.
R10	3R152-P102J	Composition: 1000 ohms $\pm 5\%$, $1/4$ w.
R11	3R152-P101J	Composition: 100 ohms ±5%, 1/4 w.
Wl	PL-19A122579-G1	RF: approx 7 inches.
W2	PL-19A122579-G2	RF: approx 10 inches.
FL1	PL-19C304250-G1	Lowpass.
mns 1	100001000 74	
TB51	19C301086-P4	Feed-thru, phen: 6 terminals; sim to G-E CR151D75406AB.
		MISCELLANEOUS
	7150186-P7	Spacer. (Used with Al).



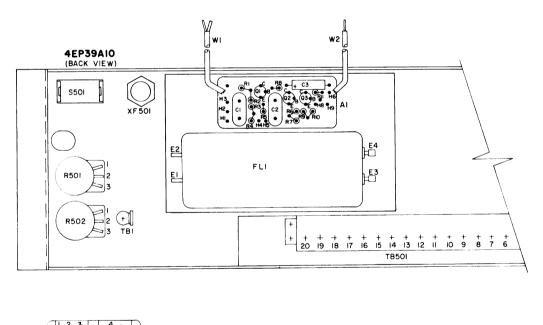
SCHEMATIC & OUTLINE DIAGRAM

FILTER-AMPLIFIER MODIFICATION MODEL 4EP38A10

SCHEMATIC DIAGRAM



OUTLINE DIAGRAM





(19C311695, Rev. 0)

SCHEMATIC & OUTLINE DIAGRAM

FILTER-AMPLIFIER MODIFICATION MODEL 4EP39A10

PARTS LIST

LB1-3830

SECOND RECEIVER MODIFICATION KIT PL-19A122460-G4

SYMBOL	G-E PART NO.	DESCRIPTION
		FILTER ASSEMBLY PL-19B205660-G1
A1		COMPONENT BOARD PL-19B205665-G1
C1 and C2	19B209243-P15	Polyester: 0,22 µf ±20%, 250 VDCW.
С3	5496267-P10	Tantalum: 22 μ f ±20%, 15 VDCW; sim to Sprague Type 150D.
Q1	19A115123-P1	TRANSISTORS
thru Q3		
		RESISTORS
R1 and R2	3R152-P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R3	3R152-P102J	Composition: 1000 ohms ±5%, 1/4 w.
R4 and R5	3R152-P202J	Composition: 2000 ohms ±5%, 1/4 w.
R6	3R152-P823J	Composition: 82,000 ohms $\pm 5\%$, $1/4$ w.
R7	3R152-P203J	Composition: 20,000 ohms $\pm 5\%$, $1/4$ w.
R8	3R152-P512J	Composition: 5100 ohms ±5%, 1/4 w.
R9	3R152-P202J	Composition: 2000 ohms ±5%, 1/4 w.
R10	3R152-P102J	Composition: 1000 ohms $\pm 5\%$, $1/4$ w.
R11	3R152-P101J	Composition: 100 ohms ±5%, 1/4 w.
Wl	PL-19A122579-G1	RF: approx 7 inches.
W2	PL-19A122579-G2	RF: approx 10 inches.
FL1	PL-19C304250-G1	Lowpass.
	7150186-P7	Spacer. (Used with Al).
	7775500-P144	Phen: 2 terminals.
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^{*}COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and G-E Part Number.

Service parts may be obtained from Authorized G-E Communication Equipment Service Stations or through any G-E Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- 1. G-E Part Number for component
- 2. Description of part
- 3. Model number of equipment
- 4. Revision letter stamped on unit

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired; or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

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